### Revisiting the

## Out of Band Resonances (OBR) of the SAFARI FDM-2-stage SQUID

- A SQUID with lower L<sub>in</sub> shifts away the OBR to the higher frequencies
- The snubber in use still damps down the OBR peak although it can be optimized for the new SQUID
- A nearby OBR could also occur which depends on the Loom-in characteristics. It won't be damped by the snubber at the summing point

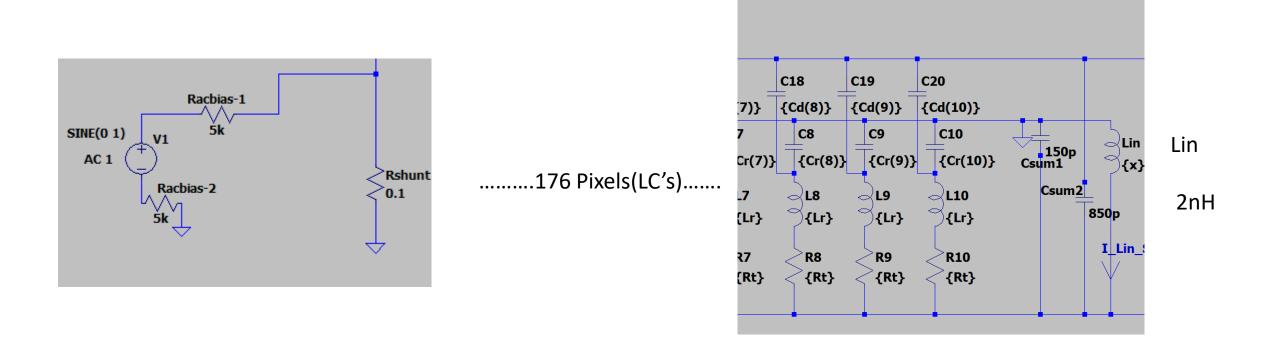
Simulation and Modeling using LTspiceXVII

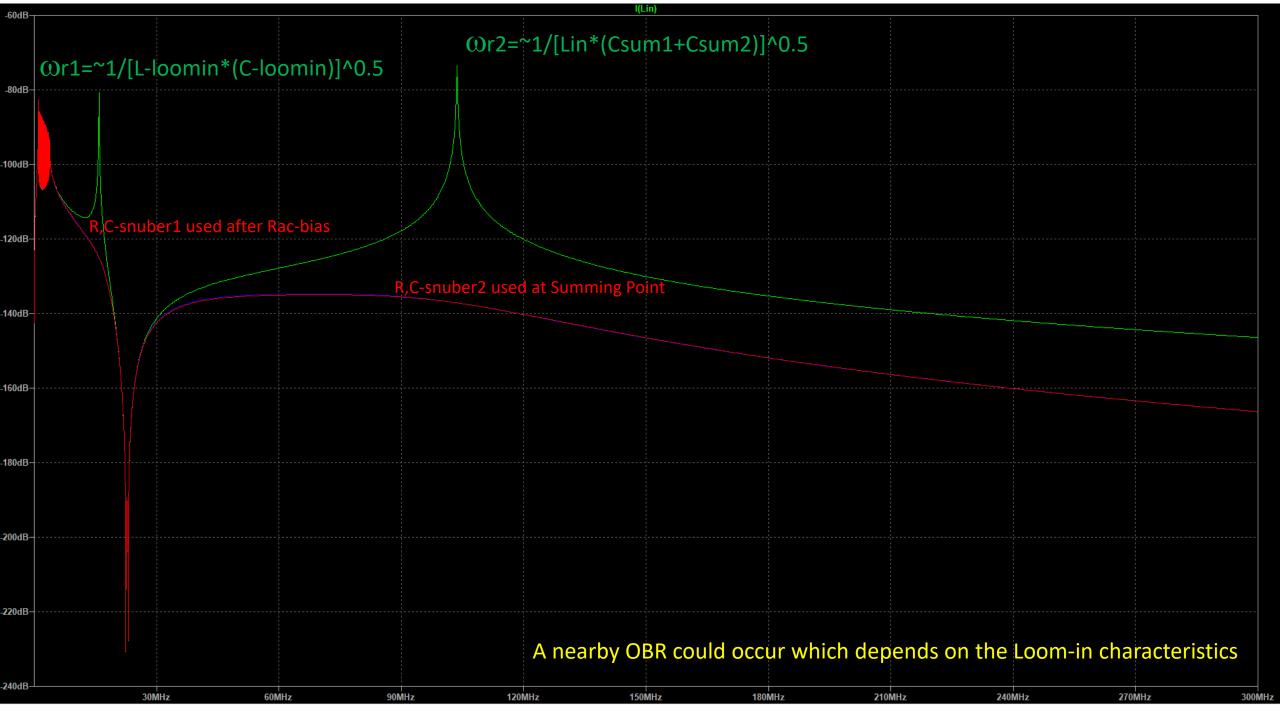
Amin Aminaei, December 2020



## Simulation of SAFARI FDM Blocks up to Input of the 1st SQUID

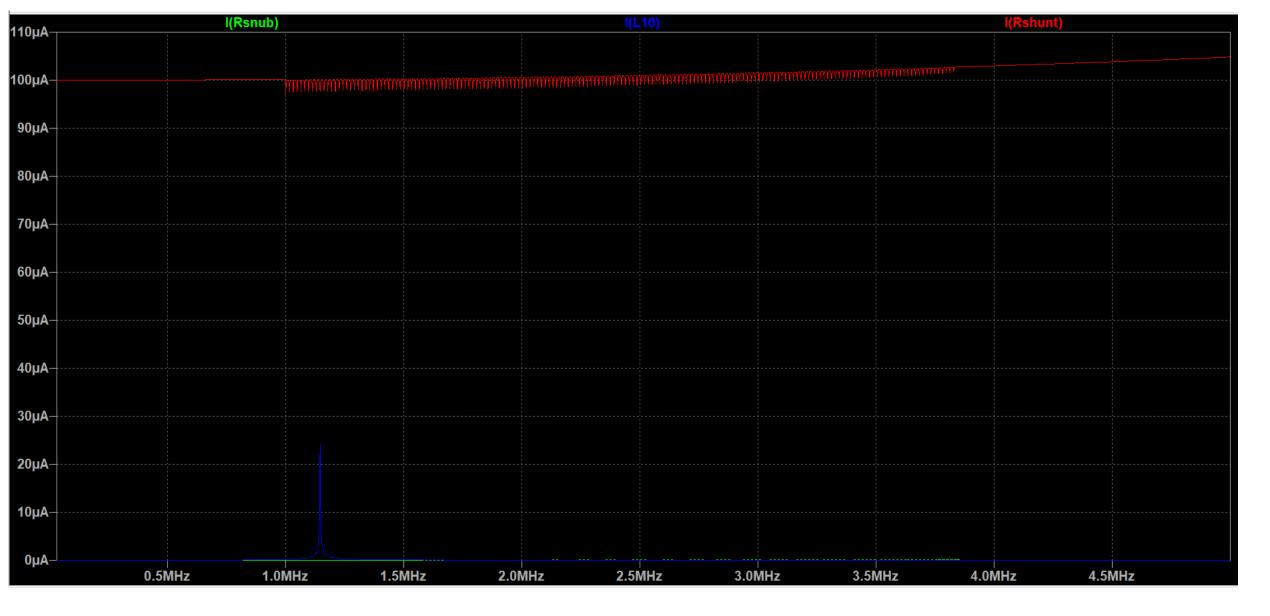




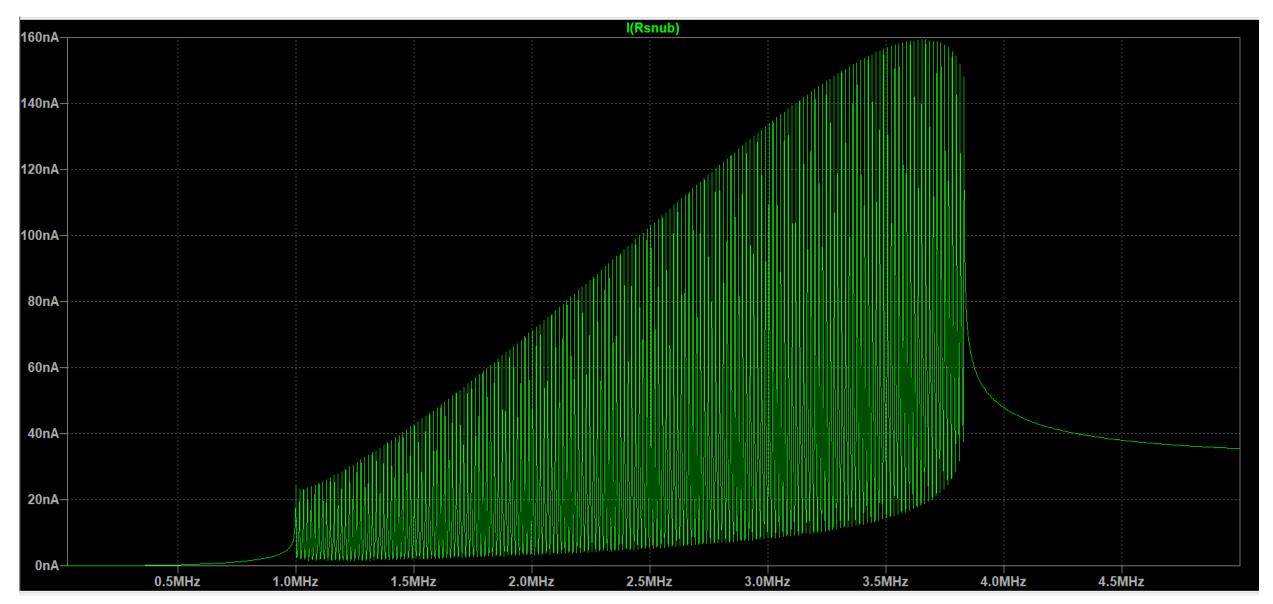


### Code (Lin=2nH):

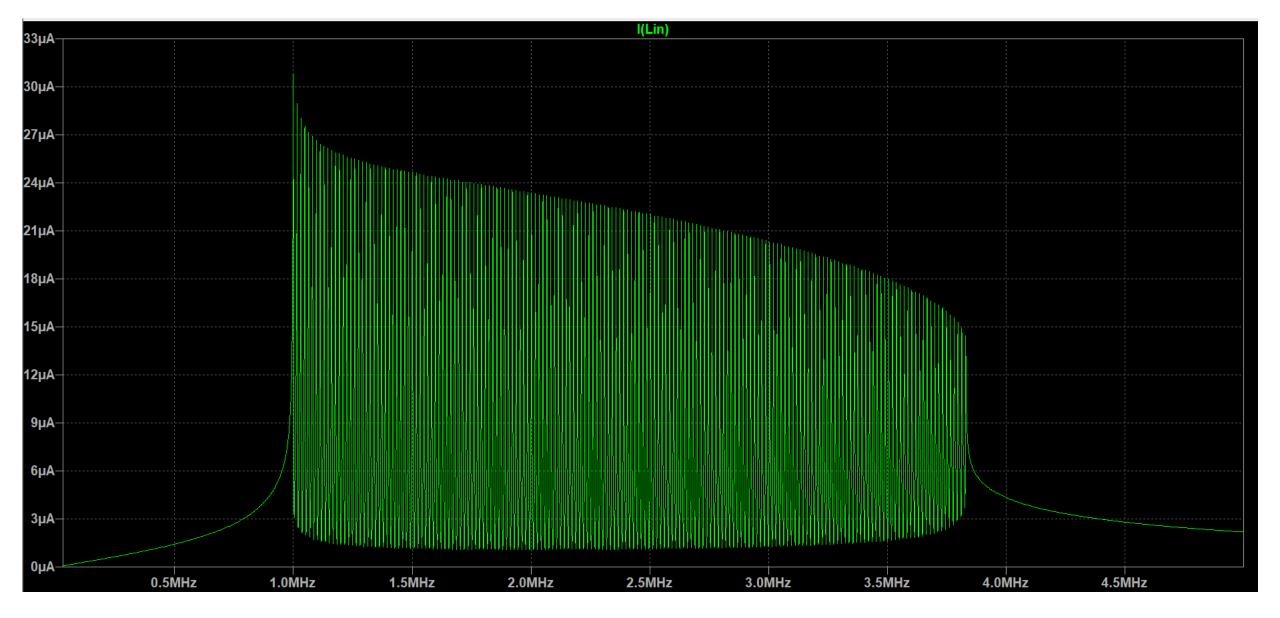
Resonators-176pix-CT-Lin-3.716MHz.asc



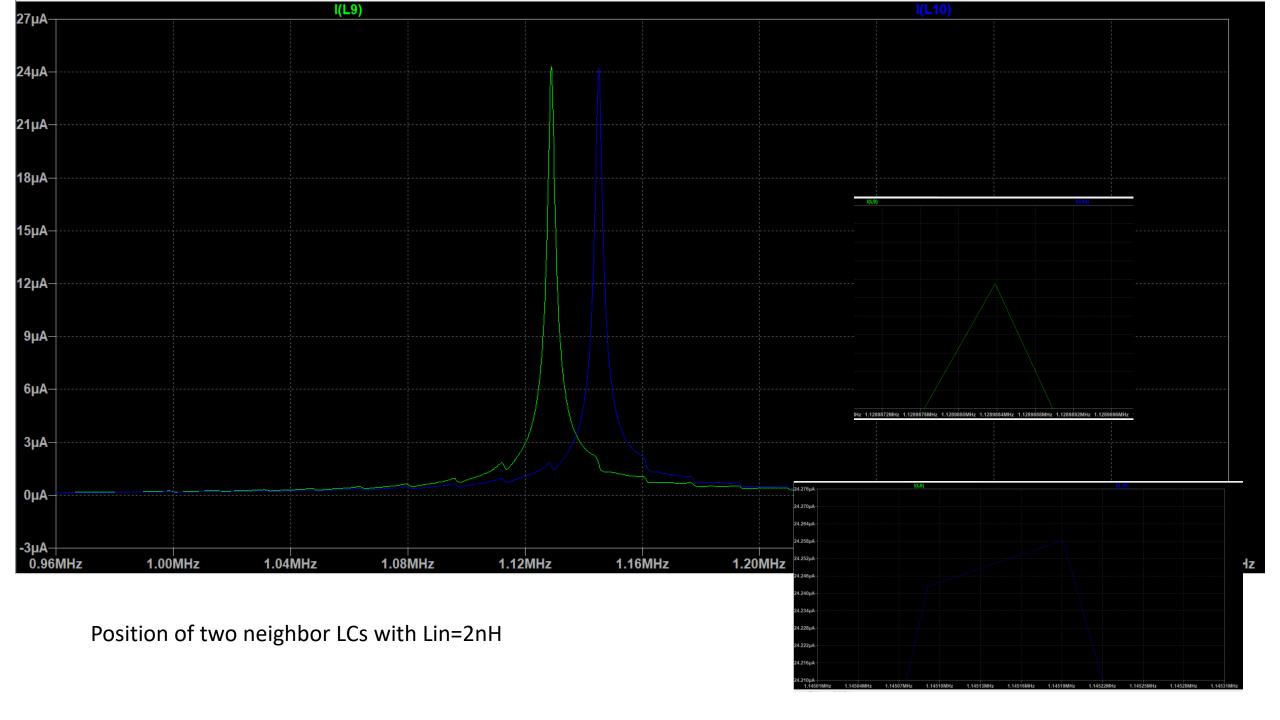
Currents of Rsnub, LC resonator#10 and Rshunt 176 LCs, AC=1V

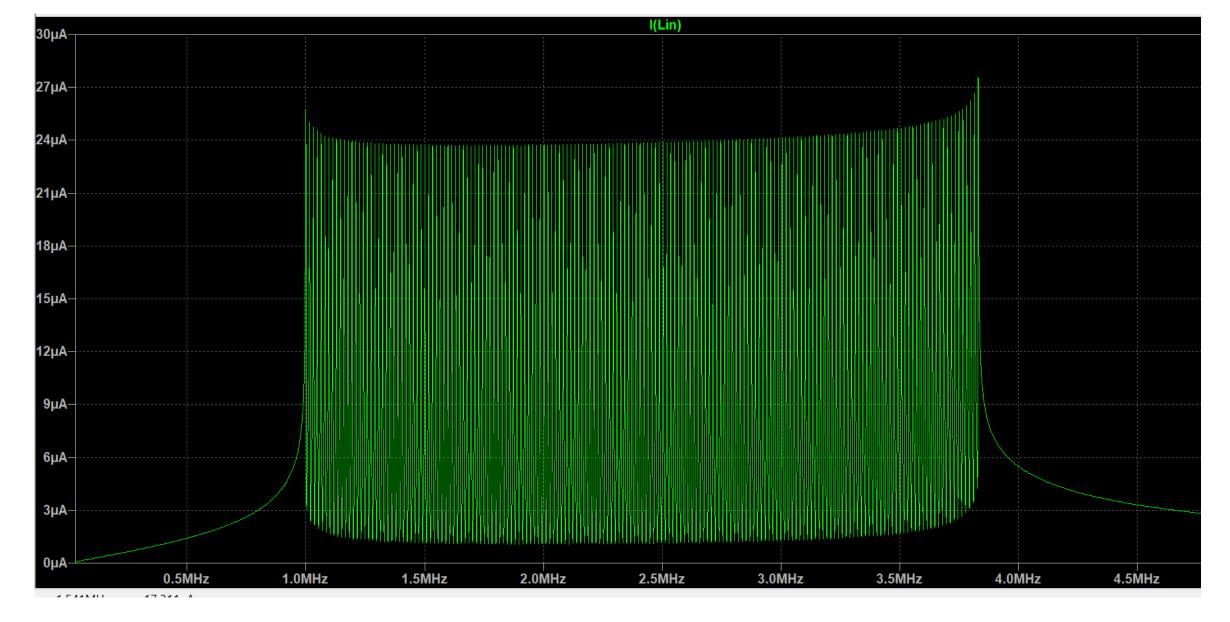


Currents of Rsnub=2.20hm, 176 LCs, AC=1V

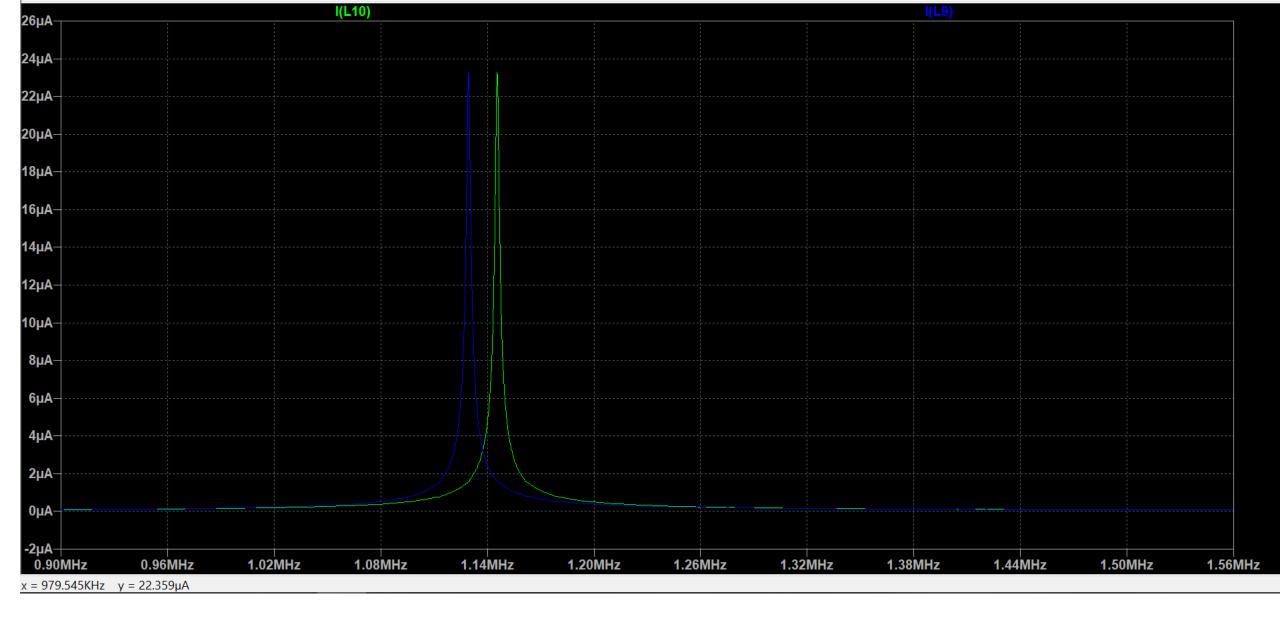


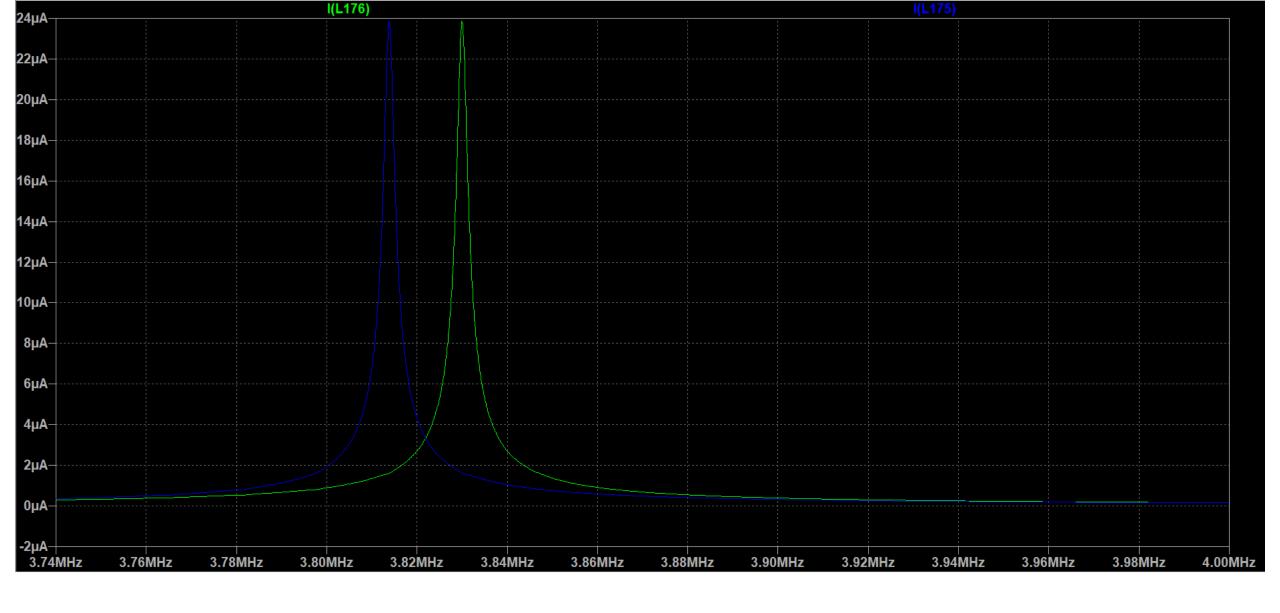
Currents of I(Lin), 176 LCs, AC=1V, Lin=2nH An illustration of current drop off at the input of SQUID at higher frequencies?



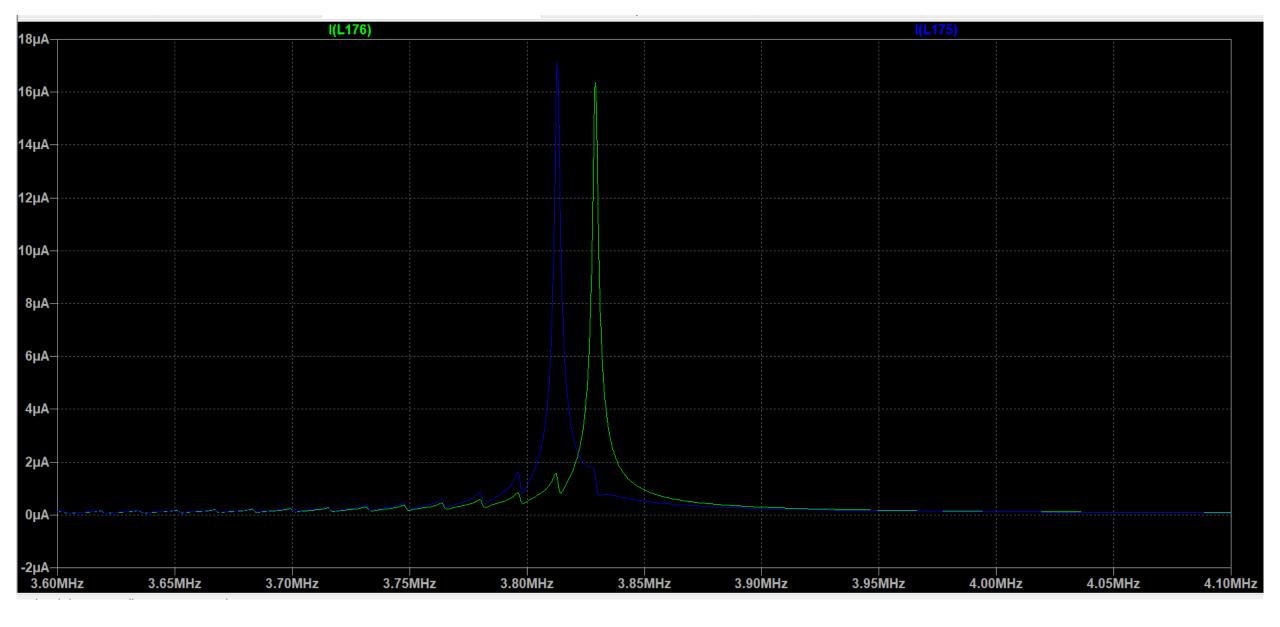


Currents of I(Lin), 176 LCs, AC=1V, Lin ~ 0





Position of two neighbor LCs with Lin~0



Position of two neighbor LCs with Lin=2nH

### Summary results

- The snubber values in the simulation (and I believe in use in the setup) are R=2.2 Ohm and C=10nf which gives the corner frequency ½.pi.(R.C)=7.23MHz (10Pf would give 7.2GHz!)
- (additional info: In the simulation, the first peak of OBR is due to the loom of AC bias around 20MHz and the second peak of OBR is due to the Common inductance and C summing points further away around 100 MHz. Snubber would damp both peaks, see the attached results)
- -The current passing through the Snubber resistor is in the order of nA as opposed to uA for the LC resonators and the shunt resistor of 0.1 Ohm. I think this has been briefly addressed by Jan in the meeting of which the current would be dominant in Rshunt since they are in parallel and Rshunt << Rsnubber.
- Please see the results in the attached file and let me know if values need to be changed. The AC voltage is 1 volt and Rs is 10 kOhm. Other parameters are Rtes=40mOhm. Lr=3uH, C ratio=9, f=1-3.8MHz, N=176 LCs. You might have measured different values but the order (uA of Rshunt current vs nA of Snubber current should still stand)

- -The max. power dissipation of Rsnubber is (160nA)^2\* 2.2=56.3 fW and for Rshunt is ~1nW.
- I've used the simplified model of resonators up to the input of SQUID to avoid complexity of harness and SQUID and FEE. I can rerun it for complete model and the number of pixels you used if needed.

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Simulation for a) common inductance of 2nH and no common inductance (S.C., in LTSpice a very small value of 0.00001fH to see
the current)
Here are the results.
Lc=2nH
Frequency shift: examples of Two neighbour resonators
Fr10=1.14519MHz
Fr9=1.12898MHz
deltaF=16.21kHz
Lc current drops off from some 30uA in 1MHz to 18Ua to 3.8MHz (see the pattern in the attached file)
Lc=0.00001fH (S.C.)
Lc current of common inductance roughly the same in the order of 24uA for all frequencies except edges (max. 27uA) see the
pattern
Fr10=1.14558MHz
Fr9=1.12938MHz
deltaF=16.2kHz
Fr10sc-Fr10=~390Hz
Fr9sc-Fr9=~400Hz
Fr175=3.81294MHz Lcom=2nH Fr176=3.82914MHz
                                                        deltaFr=16.2kHz
Fr175sc=3.81383MHz
Fr176sc=3.83003MHz
```

Fr176sc-Fr176=890Hz

Fr175sc-Fr175=890Hz highest frequency shift for 176 LC resonators.

deltaFr=16.2kHz

- (1) the power dissipation is higher when having a higher common inductance.
- (2) the power dissipation is higher when with lower TES resistance (lower in transition).
- (3) the highest power dissipation comes from shunt resistance which is around 1.05 nW.
- (4) the higher the Rac bias, the lower current, so lower power dissipation. Actually now we use 50 kOhm, so should be safe.
- (5) the impedance of AC bias loom influence is not significant.
- (6) the longer The AC bias loom, the higher power dissipation.
- (7) if the loom is very long, will be 3.5 MHz unwanted resonance.

- A cryogenic LNA as a reference performance for in use FEEs.

Some technical info:

Frequency starts at 1 MHz (where FDM begins )and goes up to 3GHz for OBR.

Good noise figure, linearity and gain
Can be used for transfer function study, open loop and BBFB

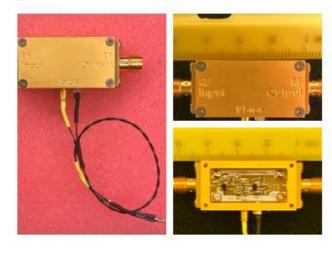
#### PRODUCT 1:

Product Details	
Part Number	BZ-P0010300-150827-152323
Manufacturer	B&Z Technology
General Parameters	
Туре	Low Noise Amplifier
Configuration	Module with Connector
Frequency	1 MHz to 3 GHz
Gain	29 to 30 dB
Gain Flatness	±1.5 dB
Noise Figure	1 to 1.3 dB
P1dB	10 to 20 dBm
P1dB	0.01 to 0.1 W
Input VSWR	2.00:1
Output VSWR	2.00:1
Sub-Category	Octave Amplifier
Supply Voltage	15 V
Current Consumption	95 mA

### • Product 2:

### 1MHz - 2GHz Cryo LNA

\$2,500.00





#### **Key Features:**

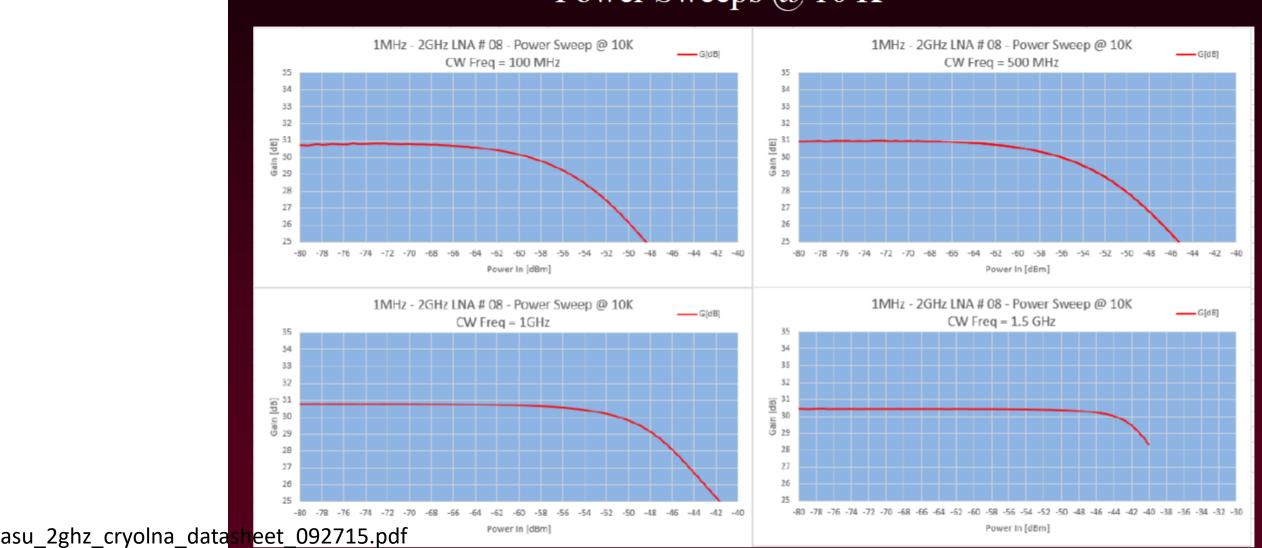
- Power gain: 30dB
- Gain Flatness: < 0.1 dB on the 10-2000MHz band</li>
- Noise temperature referenced to the input of LNA: 4-5 Kelvin
  - ( Noise figure < 0.075 dB)</li>
- Input and output Impedance: 50 OHM
- Input retun loss: < -10dB</li>
- Output retun loss: < -10dB</li>
- RF connectors: SMA female for Input and output
- Unconditionally stable with any input / output impedance
- Input 1dB Compression @ 1GHz: -50dBm
- Power consumption: 10mW at 10K

http://thz.asu.edu/products.html

# Linearity Measurements:

# 1dB Gain Compression Point @ 10K

## Power Sweeps @ 10 K



## Linearity Measurements:

## 1dB Gain Compression Point @ 300K

### Power Sweeps @ 300 K

